





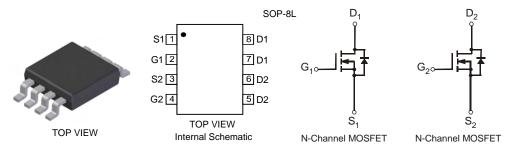
DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Dual N-Channel MOSFET
- Low On-Resistance
 - 24mΩ @ V_{GS} = 4.5V
 - $29m\Omega$ @ $V_{GS} = 2.5V$
 - 37mΩ @ V_{GS} = 1.8V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072g (approximate)



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units	
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Drain Current (Note 1)	Steady State	T _A = 25°C T _A = 70°C	I _D	8 6.7	А
Pulsed Drain Current (Note 3)			I _{DM}	30	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P _D	1.3	W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	96	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

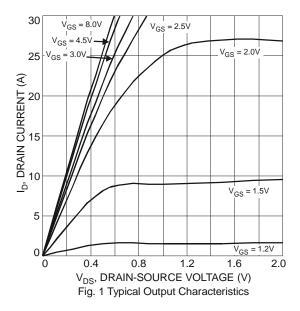
- 1. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 2. No purposefully added lead.
- 3. Repetitive rating, pulse width limited by function temperature.
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

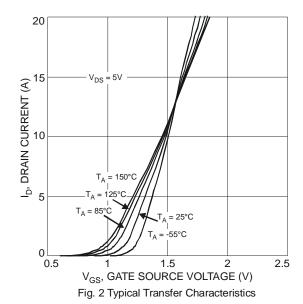


Electrical Characteristics @T_A = 25°C unless otherwise specified

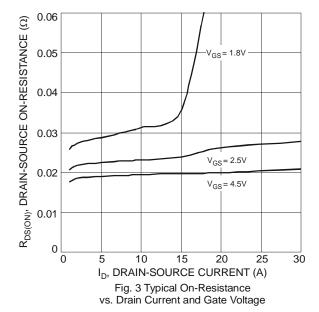
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV_{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 20V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(th)}$	0.5	_	0.9	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
			19	24		$V_{GS} = 4.5V, I_D = 8.2A$	
Static Drain-Source On-Resistance	R _{DS} (ON)	_	23	29	mΩ	$V_{GS} = 2.5V, I_D = 3.3A$	
	, ,		29	37		$V_{GS} = 1.8V, I_D = 2.0A$	
Forward Transfer Admittance	Y _{fs}	_	7		S	$V_{DS} = 10V, I_D = 4A$	
Diode Forward Voltage (Note 5)	V_{SD}	0.5	_	0.9	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	Ciss	_	867	_	pF	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Output Capacitance	Coss	_	85	_	pF	$V_{DS} = 15V, V_{GS} = 0V$	
Reverse Transfer Capacitance	C _{rss}	_	81	_	pF	f = 1.0MHz	
Gate Resistance	R_{G}	_	1.29	_	Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$	
SWITCHING CHARACTERISTICS							
Total Gate Charge	Q_g	_	8.8	_	nC		
Gate-Source Charge	Qgs	_	1.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 8.2A$	
Gate-Drain Charge	Q_{gd}	_	3.0	_	nC		
Turn-On Delay Time	t _{d(on)}	_	13.2	_	ns		
Turn-On Rise Time	t _r	_	12.6	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{d(off)}		64.8		ns	$R_L = 10\Omega$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _f		21.7	_	ns		

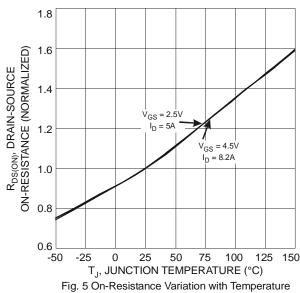
Notes: 5. Short duration pulse test used to minimize self-heating effect.

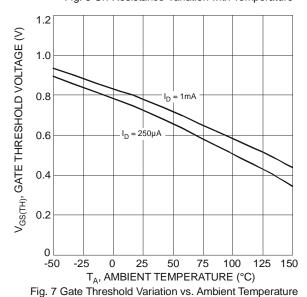












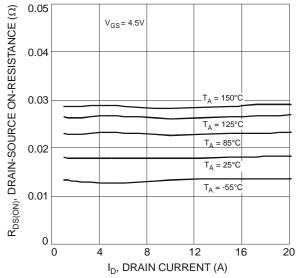


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

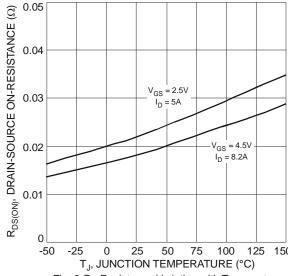


Fig. 6 On-Resistance Variation with Temperature

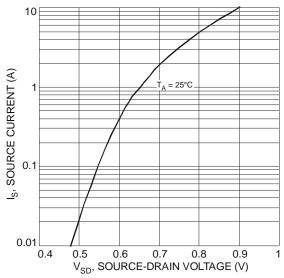
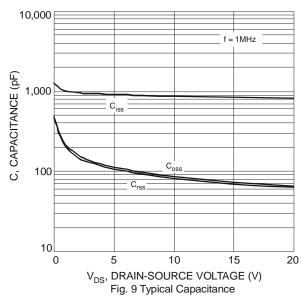


Fig. 8 Diode Forward Voltage vs. Current





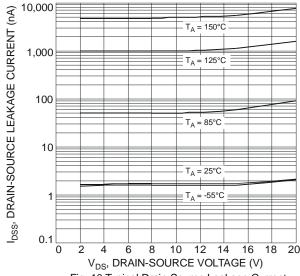


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

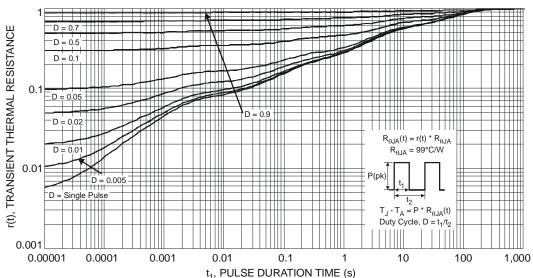


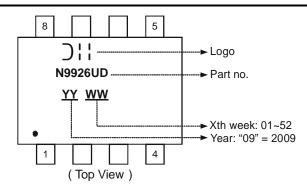
Fig. 11 Transient Thermal Response

Ordering Information (Note 6)

Part Number	Case	Packaging
DMG9926USD-13	SOP-8L	2500/Tape & Reel

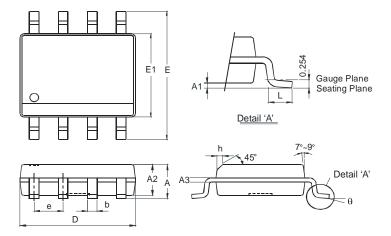
Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



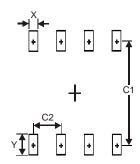


Package Outline Dimensions



SOP-8L				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	1	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27



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